

IN THE SPECIFICATION:

Please replace paragraph [0021] with the following amended paragraph:

[0021] The organosilicon compounds are oxidized during deposition, preferably by reaction with oxygen (O_2) or oxygen containing compounds such as nitrous oxide (N_2O), carbon monoxide (CO), carbon dioxide (CO_2), and water (H_2O), preferably O_2 and N_2O . Organosilicon compounds that contain oxygen ~~way~~ may be decomposed to provide the oxygen. The deposited film ~~are~~ is further defined as having an atomic ratio of carbon to silicon (C:Si) in the film of less than about 1:1. Preferably, the carbon to silicon ratio in the film is between about 1:9 and about 3:4. The deposited films formed from oxidized organosilicon compounds have dielectric constants of less than about 3.0 and low moisture content.

Please replace paragraph [0038] with the following amended paragraph:

[0038] When susceptor 12 and the wafer are in processing position ~~[[14]]~~, they are surrounded by an insulator 17 and process gases exhaust into a manifold 24. During processing, gases inlet to manifold 11 are uniformly distributed radially across the surface of the wafer. A vacuum pump 32 having a throttle valve controls the exhaust rate of gases from the chamber.

Please replace paragraph [0047] with the following amended paragraph:

[0047] Fig. 2 shows an illustrative block diagram of the hierarchical control structure of the computer program 410. A user enters a process set number and process chamber number into a process selector subroutine 420 in response to menus or screens displayed on ~~the a~~ CRT monitor ~~[[40]]~~ [[40]] ~~(not shown)~~ by using ~~the a~~ light pen ~~[[44]]~~ [[44]] ~~(not shown)~~ interface. The process sets are predetermined sets of process parameters necessary to carry out specified processes, and are identified by predefined set numbers. The process selector subroutine 420 the (i) selects a desired process

chamber on a cluster tool such as an Centura® platform (available from Applied Materials, Inc.), and (ii) selects a desired set of process parameters needed to operate the process chamber for performing the desired process. The process parameters for performing a specific process relate to process conditions such as, for example, process gas composition and flow rates, temperature, pressure, plasma conditions such as RF bias power levels and magnetic field power levels, cooling gas pressure, and chamber wall temperature and are provided to the user in the form of a recipe. The parameters specified by the recipe are entered utilizing the light pen/CRT monitor interface.